

Silicon NPN Power Transistors

2SC3857

DESCRIPTION

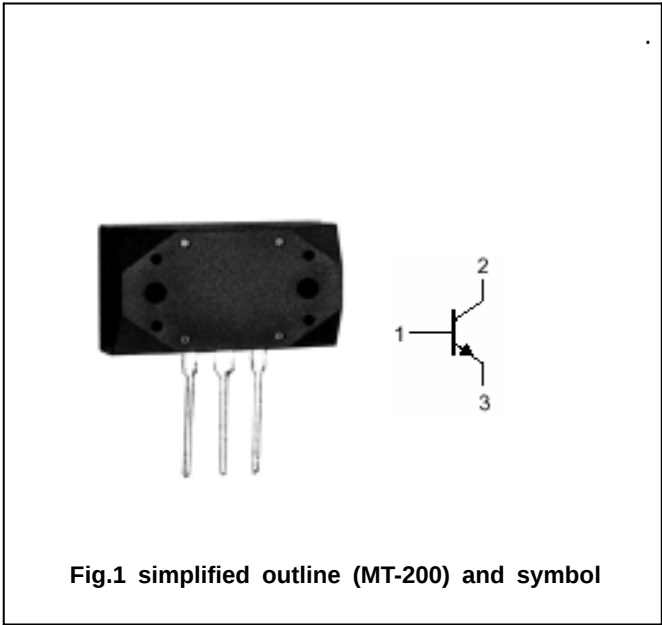
- With MT-200 package
- Complement to type 2SA1493

APPLICATIONS

- Audio and general purpose

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25	150	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA; I_B=0$	200			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=10A; I_B=1A$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V; I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V; I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=5A; V_{CE}=4V$	50		180	
f_T	Transition frequency	$I_E=-0.5A; V_{CE}=12V$		20		MHz
C_{OB}	Output capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		250		pF

Switching times

t_{on}	Turn-on time	$I_C=5A; R_L=12\Omega$ $I_{B1}=-I_{B2}=0.5A$ $V_{CC}=60V$		0.30		μs
t_s	Storage time			2.40		μs
t_f	Fall time			0.40		μs

◆ h_{FE} classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

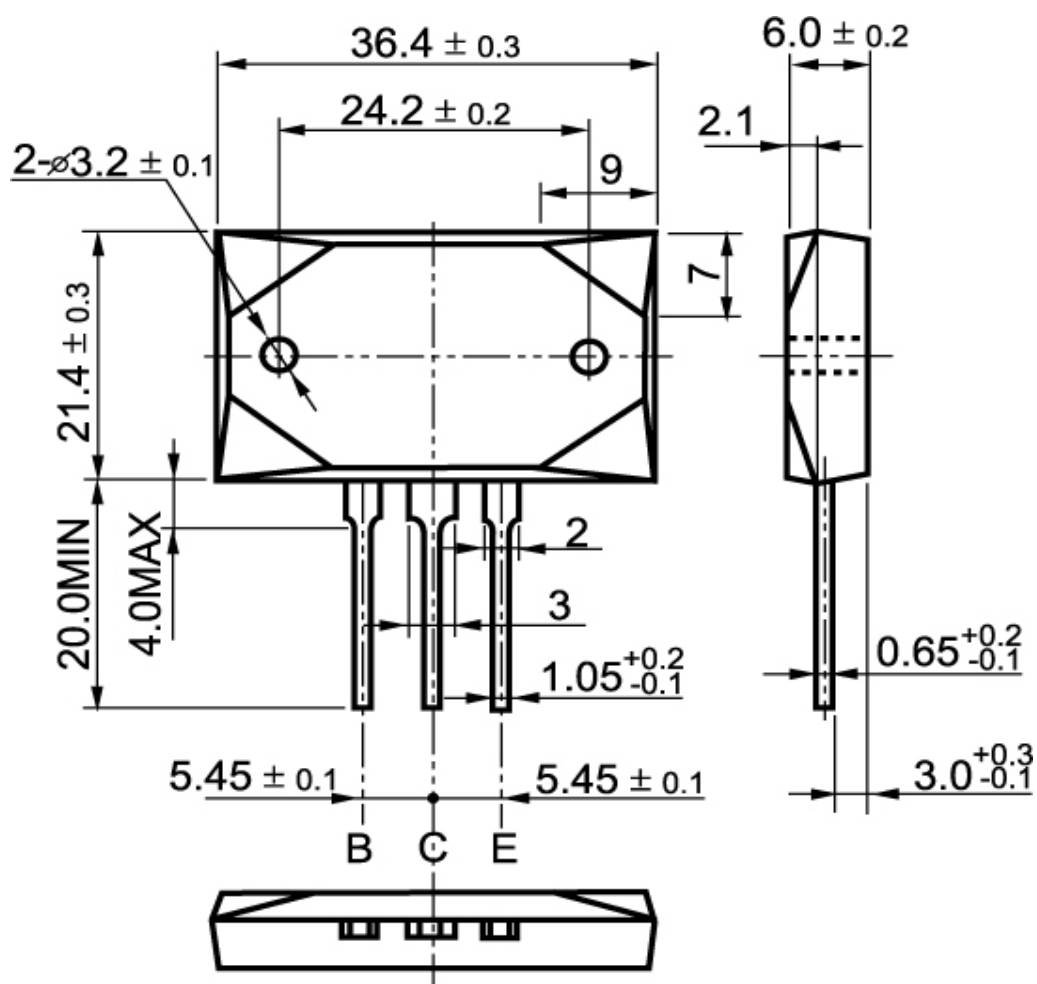


Fig.2 Outline dimensions

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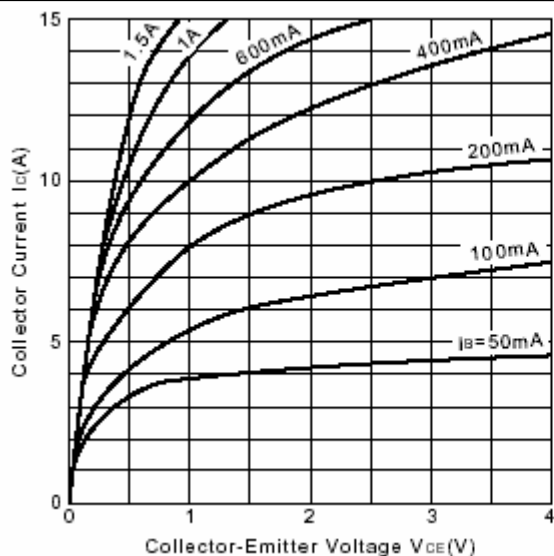


Fig.3 Static Characteristic

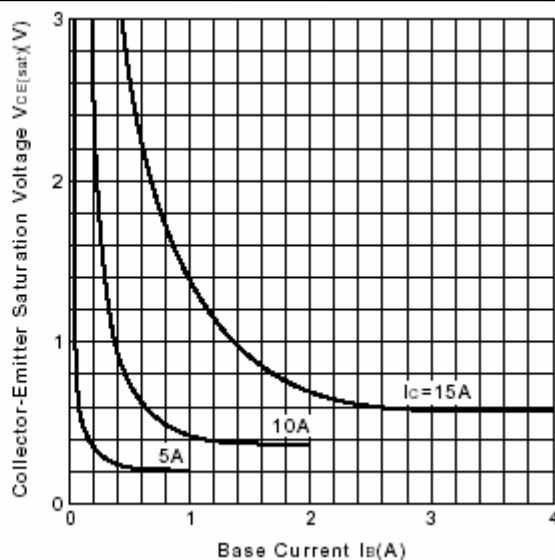
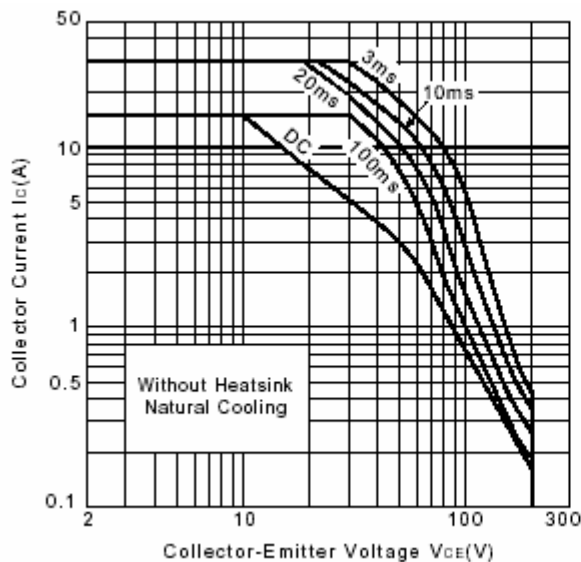
Fig.4 $V_{CE(sat)}$ - I_B Characteristics

Fig.5 Safe Operating Area

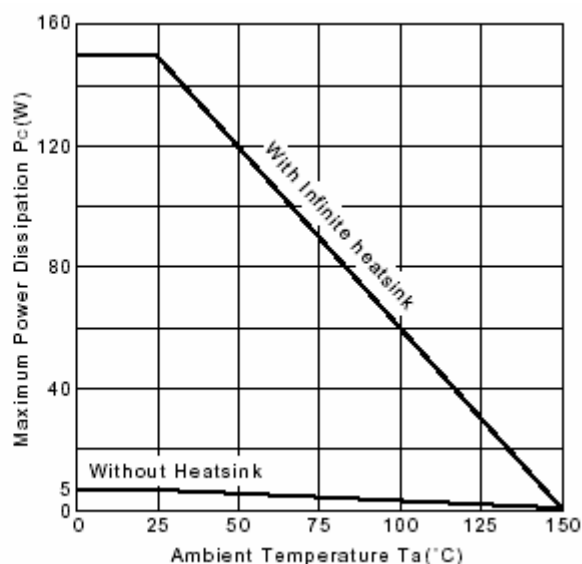
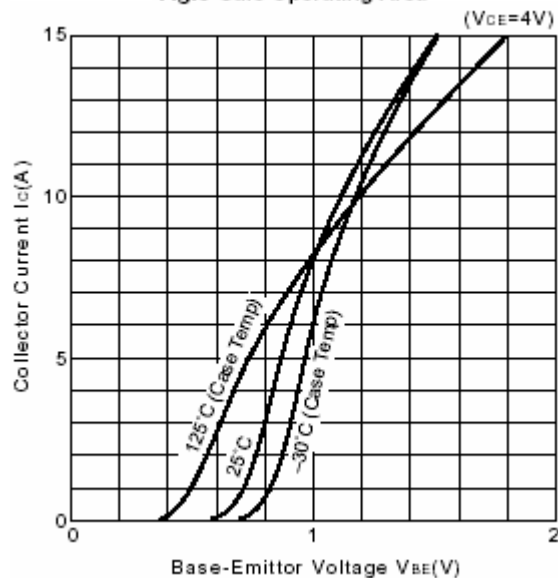
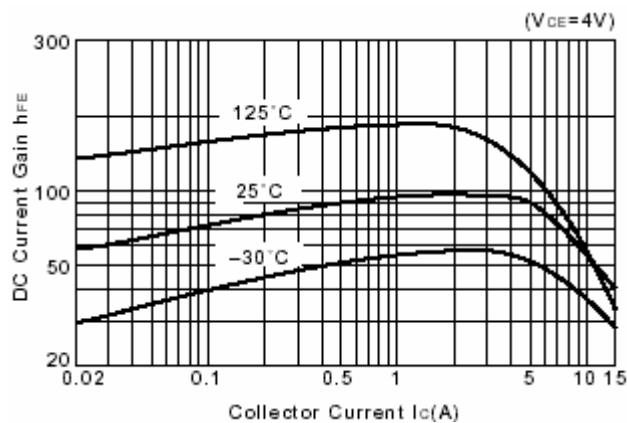
Fig.6 P_C - T_a DeratingFig.7 I_C - V_{BE} 

Fig.8 DC current Gain